

PE10B-SI-D0

Photodiode detector for laser energy measurement up to 81 nJ.



PRODUCT FAMILY KEY FEATURES

VERY LOW NOISE LEVEL

Take measurements with a noise level as low as 8 fJ (model PE3B-Si only) with the M-LINK, MAESTRO and S-LINK monitors.

3 SENSORS AVAILABLE

- $\bullet~$ PE-B-SI family: 3 and 10 mm Ø silicon sensors for 0.21 to 1.08 μm
- PE5B-GE: 5 mm Ø, germanium sensor for 0.8 to 1.65 μm
- PE3B-IN: 3 mm Ø, InGaAs sensor for 0.9 to 1.7 μm

SMART INTERFACE

Containing all the calibration data

COMPATIBLE STAND

STAND-D-233

SPECIFICATIONS

210 - 1080 nm
30 µs
1000 Hz
81 nJ
1.5 pJ
10 µs
±18 % (210 - 229 nm) ±8.0 % (230 - 254 nm) ±6.5 % (255 - 399 nm) ±2.5 % (400 - 899 nm) ±4.0 % (900 - 1009 nm) ±7.5 % (1010 - 1080 nm)

This detector is NIST-traceable at the calibration wavelength of 634 nm. Typical values are used at other wavelengths.
At 634 nm. See curves for maximum power at other wavelengths.

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PE10B-Si-IDR-D0

3. Nominal value. Actual value depends on environmental electromagnetic interference and wavelength.

DAMAGE THRESHOLDS	
Maximum average power density	65 MW/cm ²
Maximum energy density	5 μJ/cm²
Maximum power	230 µW
PHYSICAL CHARACTERISTICS	
Aperture diameter	10 mm
Absorber	SiUV
Dimensions	38.1Ø x 27.4D mm
Weight	0.09 kg
Distance to sensor face	13.7 mm
ORDERING INFORMATION	

Specifications are subject to change without notice. Refer to the user manual for complete specifications.

INTERESTED IN THIS PRODUCT?

GET A QUOTE

Find your local sales representative at gentec-eo.com/contact-us